

	Type	L #	Hits	Search Text	DBs
1	BRS	L1	0	frost near rex.in.	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
2	BRS	L2	4	sivakumar near swaminathan.in.	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
3	BRS	L3	16022	(photoresist near15 opening)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
4	BRS	L4	11433	(photoresist near5 opening)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	Type	L #	Hits	Search Text	DBs
5	BRS	L5	68	(photoresist near5 opening) near15 (solvent)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
6	BRS	L6	1	((photoresist near5 opening) near15 (solvent)) near15 (thermal or heat\$3)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
7	BRS	L7	1	((photoresist near5 opening) near15 (solvent)) near15 (heat\$3)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
8	BRS	L8	110	((photoresist near5 opening)) near15 (heat\$3)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	Type	L #	Hits	Search Text	DBs
9	BRS	L9	4	((photoresist near5 opening)) near15 (heat\$3) near15 (dimension)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
10	BRS	L10	19	((photoresist near5 opening)) near15 (heat\$3) near15 (etch\$3)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
11	BRS	L11	53	((photoresist near5 opening)) near15 (heat\$3) near15 (pattern\$3)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	U	1	Document ID	Title
1			US 20020088608 A1	Method and apparatus for heating a wafer, and method and apparatus for baking a photoresist film on a wafer
2			US 6730458 B1	Method for forming fine patterns through effective glass transition temperature reduction
3			US 6210868 B1	Method for forming a pattern on a chemical sensitization photoresist
4			US 6730458 B	Formation of fine pattern on substrate comprises forming photoresist layer on substrate, exposing portions of photoresist layer with radiation, developing exposed photoresist layer, and exposing first photoresist pattern to radiation